

SANYO Semiconductors

DATA SHEET

DCB010 — Silicon Epitaxial Planar Type (Cathode Common) Very High-Speed Switching Diode

Features

- · Ideally suited for use in hybrid ICs because of very small-sized package.
- Fast switching speed.
- Small interterminal capacitance.

Specifications

Absolute Maximum Ratings at Tc=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	VRM		85	V
Reverse Voltage	VR		80	V
Peak Forward Current	IFM		300	mA
	IFM*		450	mA
Average Rectified Current	IO		100	mA
	IO*		150	mA
Surge Current (1µs)	IFSM		4	А
	IFSM*		6	А
Allowable Power Dissipation	P		200	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

* : Total value

Electrical Characteristics at Tc=25°C

Parameter	Symbol	Conditions	Ratings			L La it
	Symbol		min	typ	max	Unit
Forward Voltage	V _{F1}	IF=1mA		0.60		V
	V _{F2}	IF=10mA		0.72		V
	VF3	IF=100mA			1.20	V
Reverse Current	I _{R1}	V _R =30V			0.1	μΑ
	I _{R2}	V _R =80V			0.5	μΑ

Marking: W6

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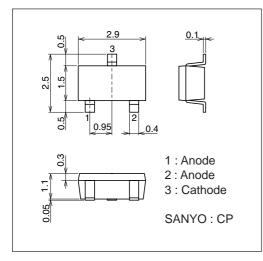
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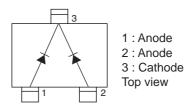
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onic
Interterminal Capacitance	С	V _R =0V, f=1MHz			3.0	pF
Reverse Recovery Time	t _{rr}	IF=10mA, VR=6V, RL=50Ω, Irr=0.1Irp			4.0	ns

Package Dimensions

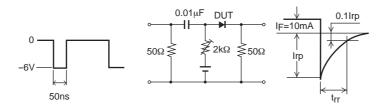
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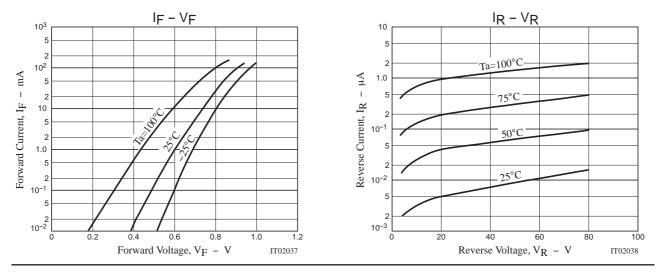


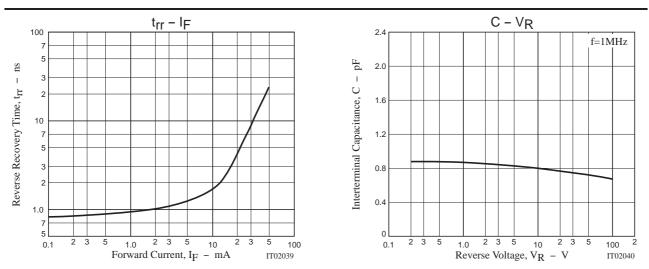
Electrical Connection



Reverse Recovery Time Test Circuit







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